Elektronische Bauelemente

SSD25P06

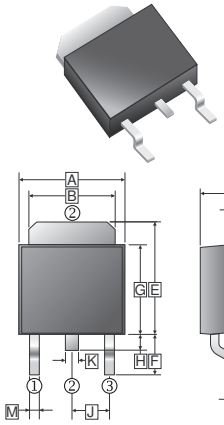
-25A, -60V, $R_{DS(ON)}$ 40mΩ
P-Ch Enhancement Mode Power MOSFET

RoHS Compliant Product
A suffix of "-C" specifies halogen free

DESCRIPTION

The SSD25P06 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent $R_{DS(ON)}$ and gate for most of the synchronous buck converter applications.
The SSD25P06 meet the RoHS and Green Product with Function reliability approved.

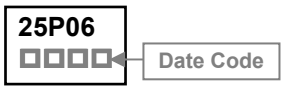
TO-252(D-Pack)

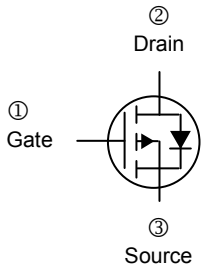


FEATURES

- $R_{DS(on)} \leqq 40m\Omega$ @V_{GS}= -10V
- $R_{DS(on)} \leqq 50m\Omega$ @V_{GS}= -4.5V
- Advanced high Cell Density Trench Technology
- Super Low Gate Charge
- Green Device Available
- TO-252 Package

MARKING





REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	6.35	6.90	J	2.336 REF.	
B	4.95	5.53	K	0.89 REF.	
C	2.10	2.50	M	0.45	1.14
D	0.665 Typ.		N	1.55 Typ.	
E	6.0	7.5	O	0	0.13
F	2.90 REF		P	0.58 REF.	
G	5.40	6.40			
H	0.60	1.20			

PACKAGE INFORMATION

Package	MPQ	Leader Size
TO-252	2.5K	13 inch

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current, @V_{GS}=10V [1]	T_C=25°C	I_D	-25	A
	T_C=100°C		-18	A
Pulsed Drain Current [2]		I_{DM}	-50	A
Power Dissipation [1]	T_C=25°C	P_D	40	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 ~ 150	°C
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	62.5	°C / W
Maximum Thermal Resistance Junction-Ambient			110	
Maximum Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	3.1	

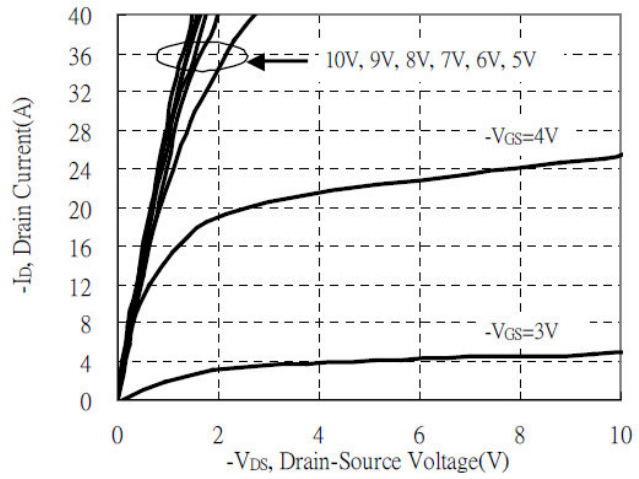
ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-Source Breakdown Voltage		BV_{DSS}	-60	-	-	V	V_{GS}=0, I_D= -250μA
Gate Threshold Voltage		$V_{GS(th)}$	-1	-	-2.5	V	V_{DS}=V_{GS}, I_D= -250μA
Forward Transfer conductance		g_{fs}	-	13	-	S	V_{DS}= -5V, I_D= -6A
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Current	T_J=25°C	I_{DSS}	-	-	-1	μA	V_{DS}= -48V, V_{GS}=0
	T_J=125°C		-	-	-25		
Static Drain-Source On-Resistance [3]		$R_{DS(ON)}$	-	33	40	mΩ	V_{GS}= -10V, I_D= -10A
			-	45	50		V_{GS}= -4.5V, I_D= -5A
Total Gate Charge		Q_g	-	38.7	-	nC	I_D= -6.2A V_{DS}= -30V V_{GS}= -10V
Gate-Source Charge		Q_{gs}	-	8.6	-		
Gate-Drain (“Miller”) Change		Q_{gd}	-	9	-		
Turn-on Delay Time		$T_{d(on)}$	-	9.7	-	Ns	V_{DD}= -30V I_D= -6A V_{GS}= -10V R_G=3Ω R_L=4.7Ω
Rise Time		T_r	-	6.2	-		
Turn-off Delay Time		$T_{d(off)}$	-	34	-		
Fall Time		T_f	-	14.3	-		
Input Capacitance		C_{iss}	-	1910	-	pF	V_{GS}=0 V_{DS}= -30V f=1.0MHz
Output Capacitance		C_{oss}	-	98.3	-		
Reverse Transfer Capacitance		C_{rss}	-	62.8	-		
Source-Drain Diode							
Diode Forward Voltage [1]		I_S	-	-	-4.2	A	
Continuous Source Current [2]		I_{SM}	-	-	-16	A	
Forward On Voltage [3]		V_{SD}	-	-0.72	-1.2	V	I_S= -1A, V_{GS}=0
Reverse Recovery Time		T_{rr}	-	32	-	nS	I_F= -6A, dI/dt=100A/μs T_J=25°C
Reverse Recovery Charge		Q_{rr}	-	44	-	nC	

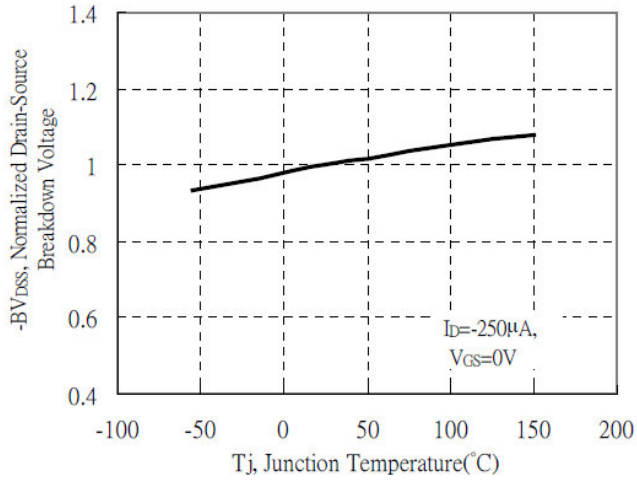
Notes:
1. The date tested by surface mounted on a 1 inch2 FR-4 board with 2oz copper.
2. The power dissipation is limited by 150°C junction temperature.
3. The data tested by pulsed, pulse width≦300us,duty cycle≦2%.

TYPICAL CHARACTERISTICS CURVE

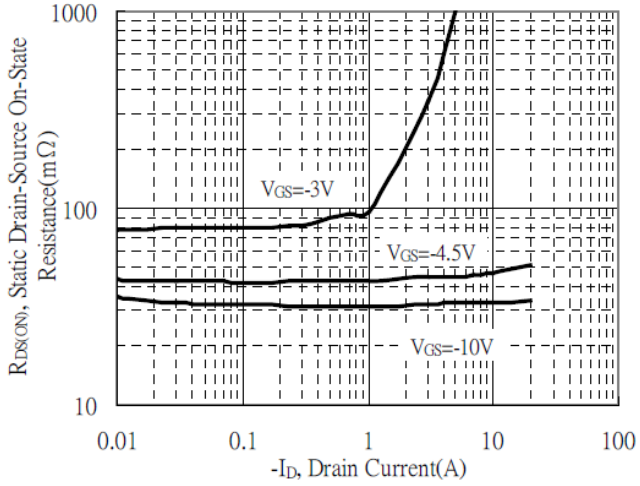
Typical Output Characteristics



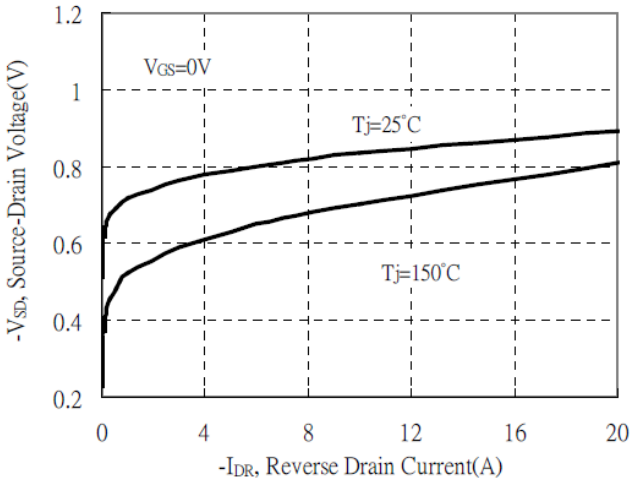
Brekdown Voltage vs Temperature



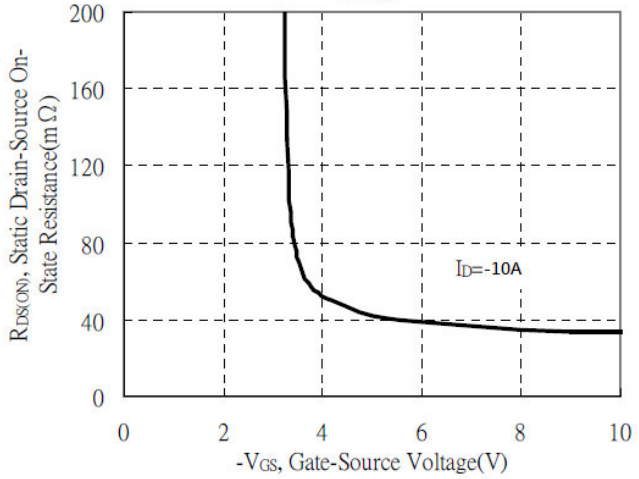
Static Drain-Source On-State resistance vs Drain Current



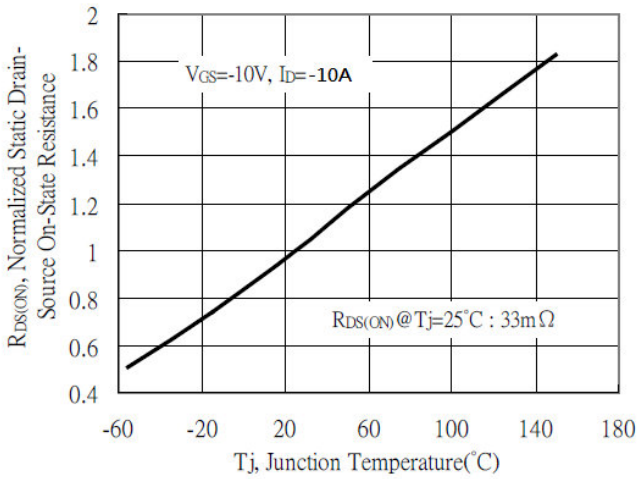
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

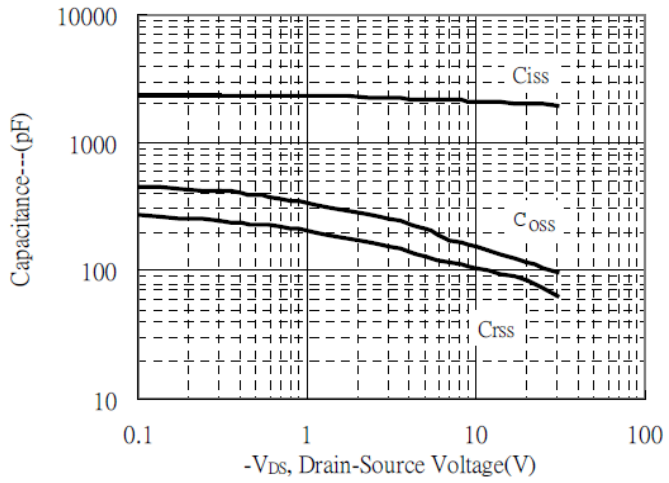


Drain-Source On-State Resistance vs Junction Tempearture

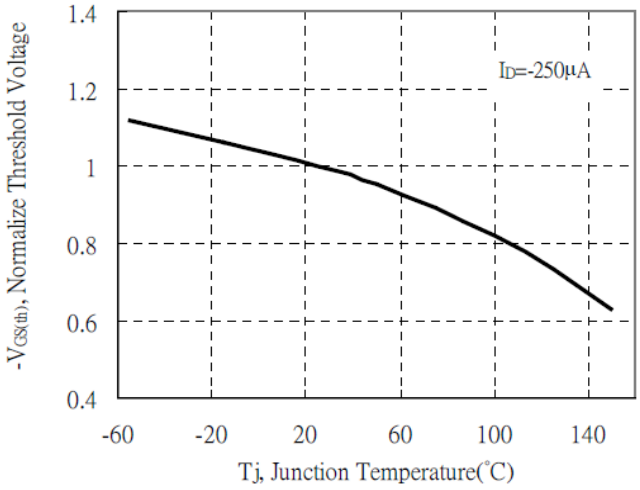


TYPICAL CHARACTERISTICS CURVE

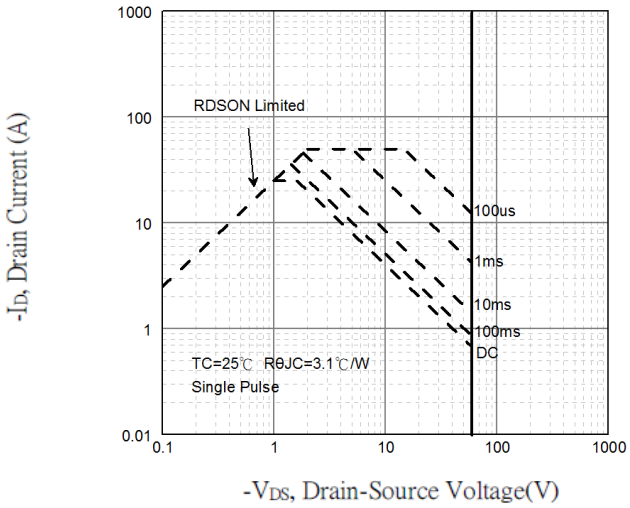
Capacitance vs Drain-to-Source Voltage



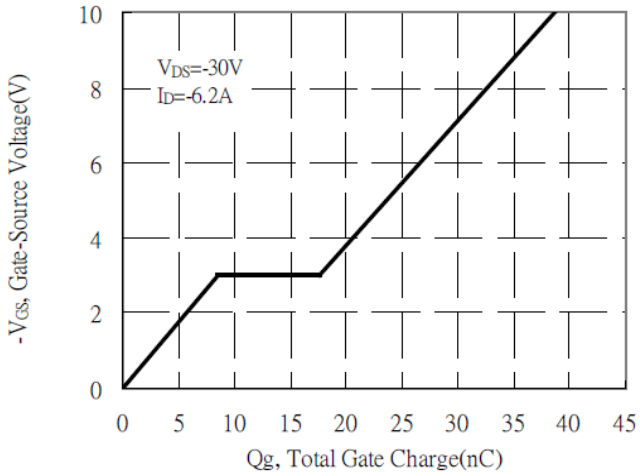
Threshold Voltage vs Junction Tempearture



Maximum Safe Operating Area



Gate Charge Characteristics



Transient Thermal Response Curves